

带输出关断的13V, 10A全集成同步升压转换器

■ 特点

- 输入电压范围 V_{IN} : 2.7V-13V
- 输出电压范围 V_{OUT} : 4.5V-13V
- 可编程峰值电流: 10A
- 高转换效率:
93% ($V_{IN} = 7.4V$, $V_{OUT} = 12V$, $I_{OUT} = 3A$)
92% ($V_{IN} = 3.6V$, $V_{OUT} = 9V$, $I_{OUT} = 1A$)
- 轻载条件下两种调制方式: 脉频调制 (PFM) 和
强制脉宽调制 (PWM)
- 集成输出关断的栅极驱动
- 低关断功耗, 关断电流1uA
- 可调节的开关频率: 200k-1.4M
- 可编程软启动
- 输出过压 (14V)、逐周期过流、热关断等保护
- DFN20L, 4.5mm*3.5mm 无铅超薄封装

■ 应用

- 无线音箱
- 便携式音箱
- 快充移动电源
- 电子烟
- USB TYPE-C 电源传输
- 拉杆音箱
- 平板电脑, 笔记本电脑
- POS机终端

■ 典型应用图

■ 概述

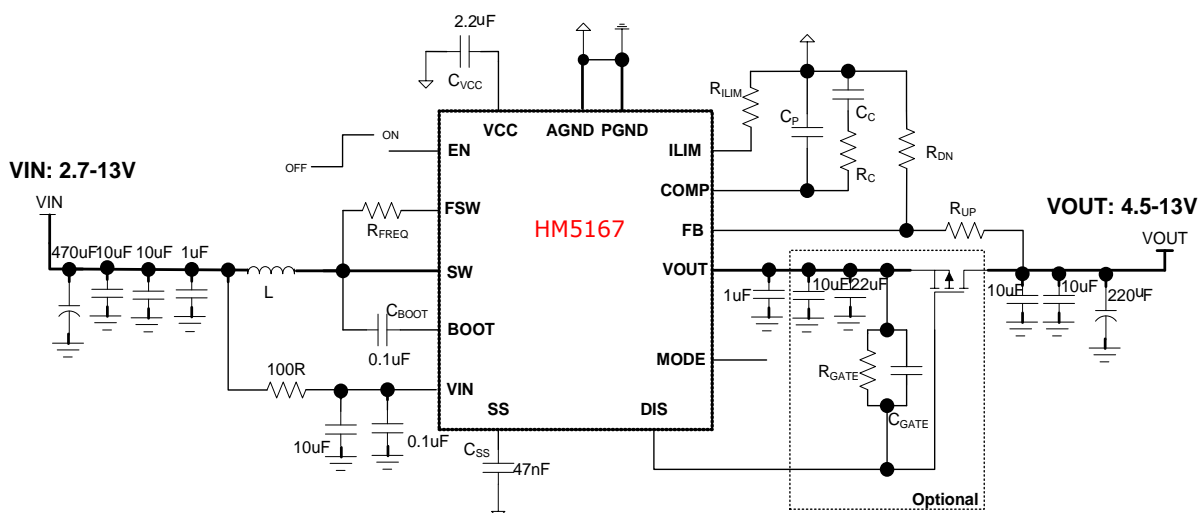
HM5167是一款高功率、全集成升压转换器, 带有负载关断功能的栅极驱动, 集成16mΩ功率开关管和23mΩ同步整流管, 为便携式系统提供高效的小尺寸解决方案。

HM5167具有2.7V至13V宽输入电压范围, 可为采用单节或两节锂电池的应用提供支持。该器件具备10A开关电流能力, 并且能够提供13V的输出电压。

HM5167采用自适应恒定关断时间峰值电流控制拓扑结构来调节输出电压。在中等到重负载条件下, HM5167工作在PWM 模式。在轻负载条件下, 该器件可通过MODE引脚选择下列两种工作模式之一。一种是可提高效率的PFM模式; 另一种是可避免因开关频率较低而引发应用问题的强制PWM模式。PWM模式下, HM5167的开关频率可通过外部电阻调节, 支持200kHz至1.4MHz的范围。

HM5167还支持可编程的软启动, 以及可调节的开关峰值电流限制。另外, HM5167集成了输出关断功能的栅极驱动, 在SD状态, 可完全断开输入电源。

此外, 该器件还提供有14V输出过压保护、逐周期过流保护和热关断保护。



13V,10A Fully-Integrated Synchronous Boost Converter with Load Disconnect Control

FEATURES

- Input voltage range V_{IN} : 2.7V to 13V
- Output voltage range V_{OUT} : 4.5V to 13V
- Programmable switch peak current limit: up to 10A
- High Efficiency
93% ($V_{IN} = 7.4V$, $V_{OUT}=12V$, $I_{OUT} = 3A$)
92% ($V_{IN} = 3.6V$, $V_{OUT}=9V$, $I_{OUT} = 1A$)
- 2 modulation mode available: PFM or PWM mode at light load
- Integrated gate driver for load disconnect and output short protection
- 1.0 μ A current consumption during shutdown
- Adjustable switching frequency: 200k to 1.4MHz
- Programmable soft start
- Output overvoltage protection (at 14V), cycle-by-cycle overcurrent protection, thermal shutdown protection
- Pb-free Packages, DFN20L, 4.5mm*3.5mm

APPLICATIONS

- Wireless/ Speakers • Portable Speakers
- Quick Charge Power Bank • E-Cigarette
- Power Interface (USB Type-C, Thunderbolt)
- POS Terminal • Tablet PC/Note Book

DESCRIPTION

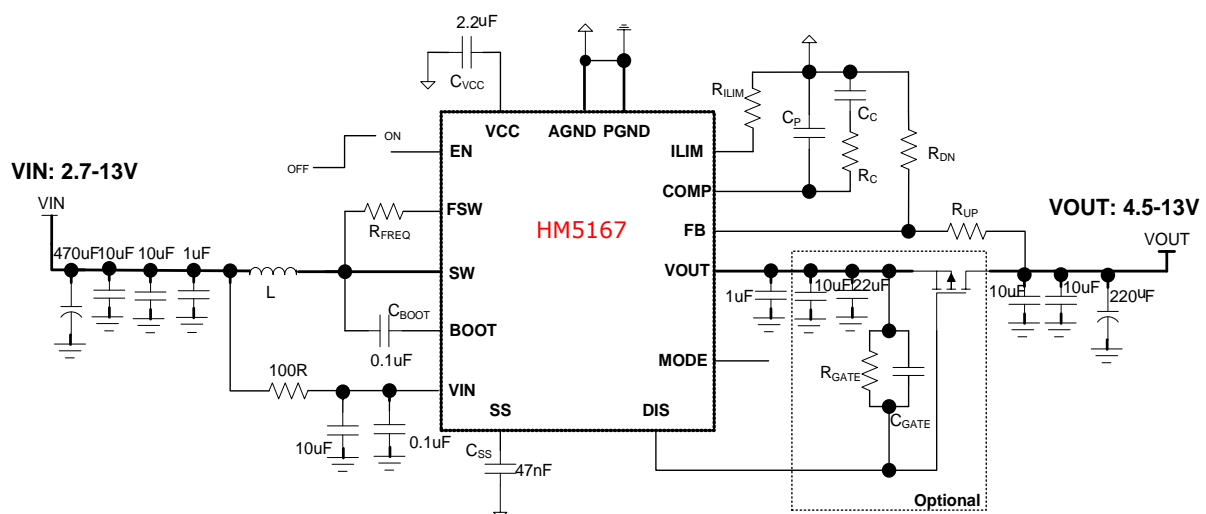
The HM5167 is a high-power density, fully integrated synchronous boost converter with a 16m Ω power switch and a 23m Ω rectifier switch to provide a high efficiency and small size solution in portable systems. The HM5167 has wide input voltage range from 2.7 V to 13 V to support applications with single cell and two cell Lithium batteries. The device has 10A switch current capability and can provide an output voltage up to 13V.

The HM5167 uses adaptive constant off-time peak current control topology to regulate the output voltage. In moderate to heavy load condition, it works in the PWM mode. In light load condition, the device has two operation modes selected by the MODE pin. One is PFM mode to improve the efficiency and another one is the forced PWM mode to avoid application problems caused by low switching frequency. The switching frequency in the PWM mode is adjustable ranging from 200kHz to 1.4MHz by an external resistor.

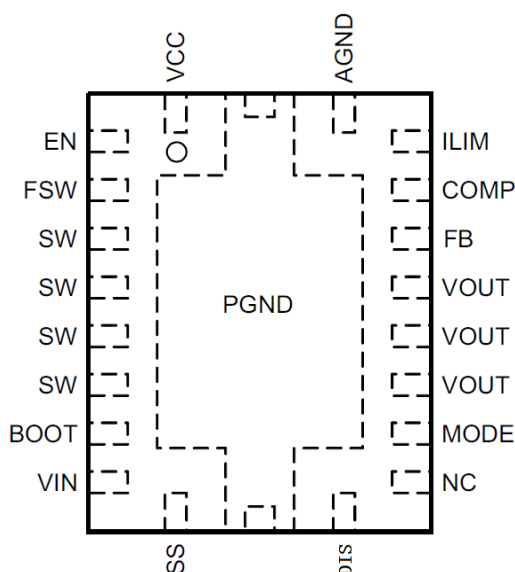
HM5167 could isolate the output from input side when shut down by a gate drive output disconnecting external FET, so that the load current consumption could be limited.

The HM5167 also implements a programmable soft-start function and an adjustable switching peak current limit function. In addition, the device provides 14V output overvoltage protection, cycle-by-cycle overcurrent protection, and thermal shutdown protection.

TYPICAL APPLICATION



■ TERMINAL CONFIGURATION



■ TERMINAL FUNCTION

Terminal No.	NAME	I/O ^{*1}	Description
1	VCC	O	Output of the internal regulator. A ceramic capacitor of 2.2uF is required between this pin and ground.
2	EN	I	Enable logic input. Logic high level enables the device. Logic low level disables the device and turns it into shutdown mode.
3	FSW	I	The switching frequency is programmed by a resistor between this pin and the SW pin.
4/5/6/7	SW	PWR	The switching node pin of the converter.
8	BOOT	O	Power supply for high-side MOSTFET gate driver. A ceramic capacitor of 0.1μF must be connected between this pin and the SW pin.
9	VIN	I	IC power supply input.
10	SS	O	Soft-start programming pin. An external capacitor connected to ground sets the ramp rate of the internal error amplifier's reference voltage during soft-start
11	DIS	O	A gate drive output for the external disconnect FET. Connect the DISDRV pin to the gate of the external FET. Leave it floating if not using the load disconnect function.
12	NC	-	No connection inside the device. Connect these two pins to ground plane on the PCB for good thermal dissipation.
13	MODE	I	Operation mode selection pin for the device in light load condition. When this pin is connected to ground, the device works in PWM mode. When this pin is left floating, the device works in PFM mode.
14/15/16	VOUT	PWR	Boost converter output.
17	FB	I	Voltage feedback.
18	COMP	O	Output of the internal error amplifier, the loop compensation network should be connected between this pin and the AGND pin.
19	ILIM	I	Adjustable switch peak current limit. An external resistor should be connected between this pin and the AGND pin.
20	AGND	-	Signal ground of the IC.
0	PGND	PWR	Power ground of the IC.

¹ I: input O: output PWR: power

■ ORDERING INFORMATION

Part Number	Package Type	Marking	Operating Temperature Range	Shipping Package / MOQ
HM5167	DFN20L	HM5167	-40°C~85°C	Tape and Reel / 5000PCS

■ ELECTRICAL CHARACTERISTIC

● Absolute Maximum Ratings^{*2}

PARAMETER		Symbol	MIN	MAX	UNIT
Voltage range	BOOT	/	-0.3	SW+7	V
	SW, FSW, V _{OUT} , DIS, V _{IN}		-0.3	14.2	
	EN, VCC, SS, COMP, MODE		-0.3	7	
	ILIM, FB		-0.3	3.6	
Operating temperature range		T _A	-40	85	°C
Operating junction temperature range		T _J	-40	150	°C
Storage temperature range		T _{STG}	-50	150	°C

● Recommended Operating Conditions

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
Input power voltage range	V _{IN}		2.7		13.2	V
IC power supply voltage range	V _{IN}		2.7		13.2	V
Output voltage range	V _{OUT}		4.5		20	V
Inductance, effective value	L		0.47	2.2	10	μH
Input capacitance, effective value	C _i		10			μF
Output capacitance, effective value	C _o		6.8	47	1000	μF
Operating temperature	T _a		-40	25	85	°C
Operating junction temperature	T _J		-40		125	°C

² Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

● Electrical Characteristics³

Condition: Ta = 25°C, VIN = 2.7V-13.2V, VOUT=4.5-13.2V, unless otherwise specified.

Power Supply

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
Input power voltage range	VIN		2.7		13.2	V
IC power supply voltage range	VIN		2.7		13.2	V
Under-voltage lockout (UVLO) threshold	VIN_UVLO	VIN rising			2.7	V
		VIN falling			2.5	V
VIN UVLO hysteresis	VIN_HYS			200		mV
VCC UVLO threshold	VCC_UVLO			2.1		V
Operating quiescent current from VIN	IQ	IC enabled, no load, VFB = 1.3V, VOUT = 12V		1		uA
Operating quiescent current from VOUT				120		
Shutdown current into VIN	ISD	IC disabled, no load, no feedback resistor divider		1		uA
VCC regulation	VCC	VIN = 3.6V, VOUT = 12V, light load		5.6		V
		VIN = 3.6V, VOUT = 12V, ILOAD = 0.5A		5.2		V

EN and Mode Input

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
EN high threshold voltage	VENH		1.5			V
EN low threshold voltage	VENL				0.4	V
EN internal pull-down resistance	REN			800		kΩ
MODE high threshold voltage	VMODEH		4			V
MODE low threshold voltage	VMODEL				1.5	V
MODE internal pull-up resistance	RMODE			800		kΩ

OUTPUT

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
Output voltage range	VOUT	Freq = 500 kHz	4.5		13.2	V
Output overvoltage protection	VOVP			14.2		V
Reference voltage at the FB pin	VREF		1.186	1.204	1.222	V
Soft-start charging current	ISS			5		uA

ERROR AMPLIFIER

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
COMP pin sink current	ISINK	VFB = VREF +200 mV, VCOMP = 1.5 V		20		uA
COMP pin source current	ISOURCE	VFB = VREF -200 mV, VCOMP = 1.5 V		20		uA
High clamp voltage at the COMP pin	VCC_LPH	VFB = 1 V, RILIM = 100 kΩ		2.3		V
Low clamp voltage at the COMP pin	VCC_LPL	VFB = 1.5 V, RILIM = 100 kΩ,		1.4		V
Error amplifier transconductance	GEA	VCOMP = 1.5 V		190		uA/V

³ Depending on parts and pattern layout, characteristics may be changed

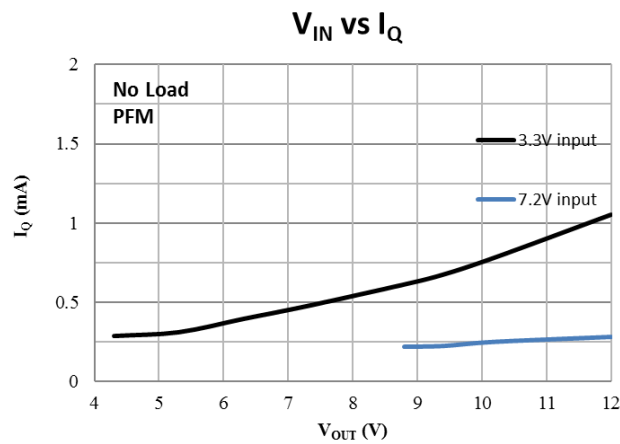
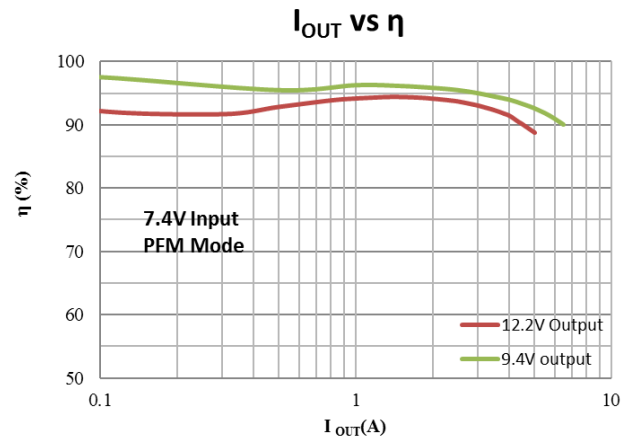
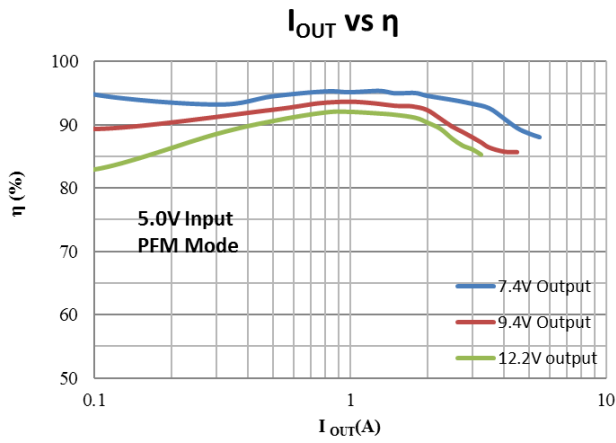
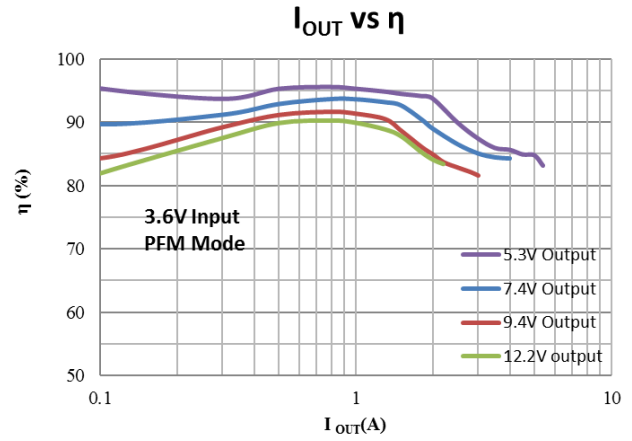
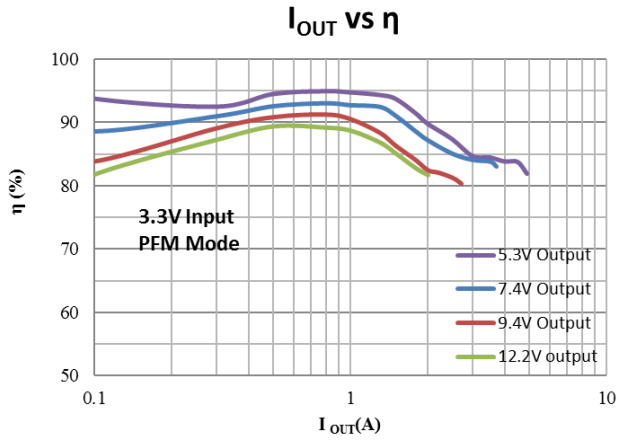
PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
POWER SWITCH						
MOSFET resistance on-	R _{DS(on)}	High-side MOSFET		23		mΩ
		Low-side MOSFET		16		mΩ
CURRENT LIMIT						
Peak switch current limit	I _{LIM}	R _{LIM} = 100 kΩ,		10.6		A
		R _{LIM} = 120 kΩ,		9.0		
Reference voltage at the ILIM pin	V _{ILIM}			1.204		V
SWITCHING FREQUENCY						
Switching frequency	f _{SW}	R _{FREQ} = 200 kΩ, V _{IN} = 5V, V _{OUT} = 12V		660		kHz
Minimum on-time	t _{ON_min}	R _{FREQ} = 200 kΩ, V _{IN} = 3.6V, V _{OUT} = 12V		190		ns
GATE DRIVER FOR LOAD DISCONNECT						
Driver current for the external FET	I _{GD_SINK}			60		uA
THERMAL SHUTDOWN						
Thermal shutdown threshold	T _{SD}			150		°C
Thermal shutdown hysteresis	T _{SD_HYS}			20		°C

● Voltage Setting Reference for HM5167

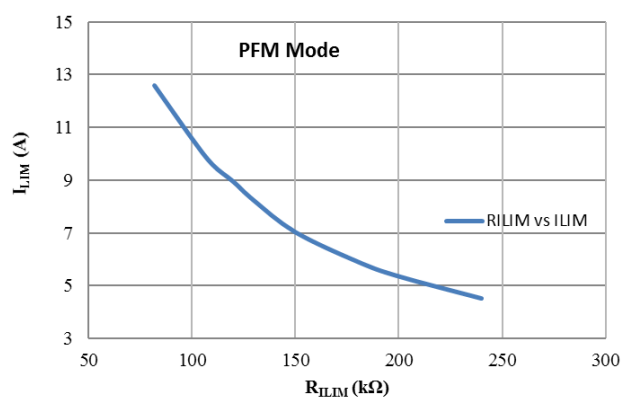
Input Power	Referred Max Input Current (RMS Value)	Input Voltage	Output Voltage	Referred Max Output Current (RMS Value)	Output Power	Efficiency	Pull-up resistor from FB	Pull-down resistor from FB
P _{Pin} (W)	I _{Pin} (A)	V _{IN} (V)	V _{OUT} (V)	I _{OUT} (A)	P _{OUT} (W)	η(%)	R _{UP} (Ω)	R _{DN} (Ω)
30.0	8.4	3.6	7.3	3.5	25.7	85.5%	510k	100k
31.8	8.8	3.6	9.3	2.8	26.1	82.2%	510k	75k
32.1	8.9	3.6	12.2	2.2	26.8	83.4%	510k	56k
44.5	8.9	5.0	7.3	5.5	39.2	88.0%	510k	100k
43.5	8.7	5.0	9.3	4.0	37.3	85.8%	510k	75k
46.2	9.2	5.0	12.2	3.2	39.4	85.2%	510k	56k
67.2	9.1	7.4	9.3	6.5	60.5	90.1%	510k	75k
68.5	9.3	7.4	12.2	5.0	60.8	88.8%	510k	56k

TYPICAL OPERATING CHARACTERISTICS

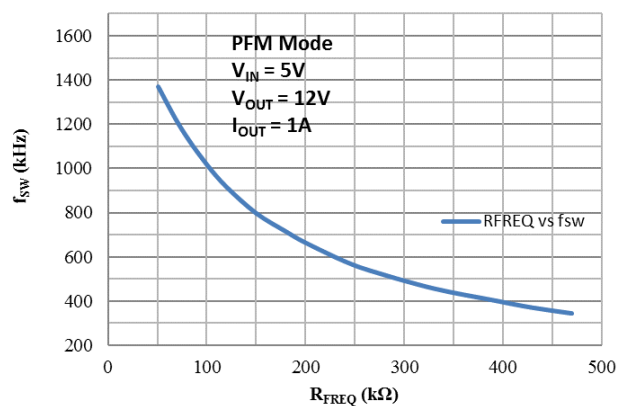
Condition: $L = 2.2\mu\text{H}$, $R_{\text{ILIM}} = 100\text{k}$, $R_{\text{FREQ}} = 200\text{k}$, Output Capacitor = $1\mu\text{F}/10\mu\text{F}/10\mu\text{F}/220\mu\text{F}$, otherwise specified.



R_{ILIM} vs I_{LIM}

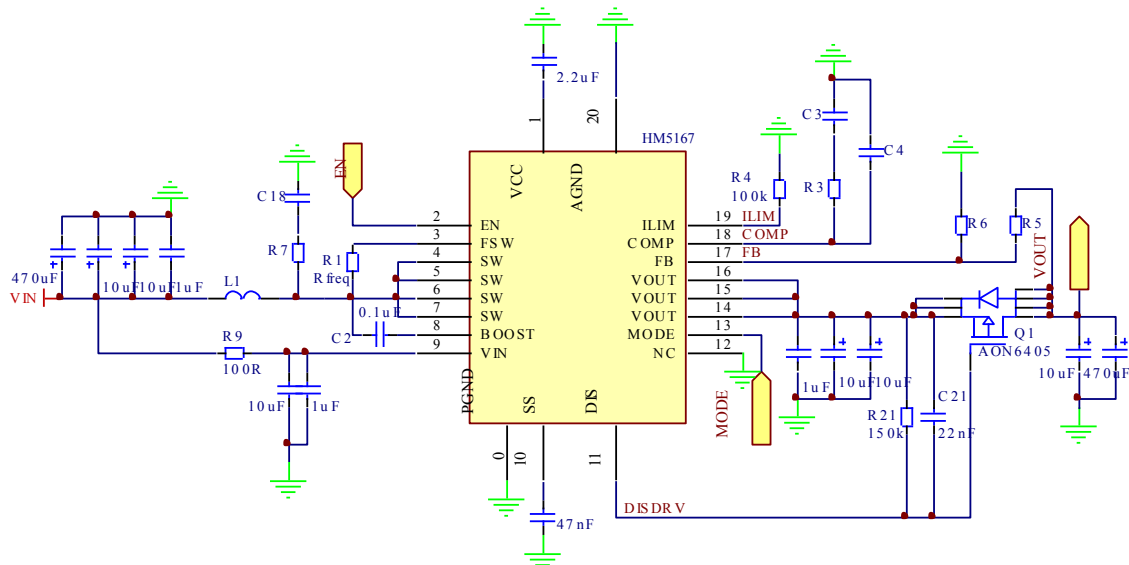


R_{FREQ} vs f_{SW}



APPLICATION INFORMATION

1. Typical Application



2. Feature Description

2.1. Functional Modes (Mode pin)

Operation

The synchronous boost converter HM5167 operates at a quasi-constant frequency pulse width modulation (PWM) in moderate to heavy load condition. Based on the V_{IN} to V_{OUT} ratio, a circuit predicts the required off-time of the switching cycle. At the beginning of each switching cycle, the low-side N-MOSFET switch is turned on, and the inductor current ramps up to a peak current that is determined by the output of the internal error amplifier. After the peak current is reached, the current comparator trips, and it turns off the low-side N-MOSFET switch and the inductor current goes through the body diode of the high-side N-MOSFET in a dead-time duration. After the dead-time duration, the high-side N-MOSFET switch is turned on. Because the output voltage is higher than the input voltage, the inductor current decreases. The high-side switch is not turned off until the fixed off-time is reached. After a short dead-time duration, the low-side switch turns on again and the switching cycle is repeated.

In light load condition, the HM5167 implements two operation modes, PFM mode and forced PWM mode, to meet different application requirements. The operation mode is set by the status of the MODE pin. When the MODE pin is connected to ground, the device works in the forced PWM mode. **When the MODE pin is left floating, the device works in the PFM mode, which is the recommended mode.**

PWM Mode

In the forced PWM mode, the HM5167 keeps the switching frequency unchanged in light load condition. When the load current decreases, the output of the internal error amplifier decreases as well to keep the inductor peak current down, delivering less power from input to output. When the output current further reduces, the current through the inductor will decrease to zero during the off-time. The high-side N-MOSFET is not turned off even if the current through the MOSFET is zero. Thus, the inductor current changes its direction after it runs to zero. The power flow is from output side to input side. The efficiency will be low in this mode. But with the fixed switching frequency, there is no audible noise and other problems which might be caused by low switching frequency in light load condition.

PFM Mode

The HM5167 improves the efficiency at light load with the PFM mode. When the converter operates in light load condition, the output of the internal error amplifier decreases to make the inductor peak current down, delivering less power to the load. When the output current further reduces, the current through the inductor

will decrease to zero during the off-time. Once the current through the high side N-MOSFET is zero, the high-side MOSFET is turned off until the beginning of the next switching cycle. When the output of the error amplifier continuously goes down and reaches a threshold with respect to the peak current of $I_{LIM} / 12$, the output of the error amplifier is clamped at this value and does not decrease any more. If the load current is smaller than what the HM5167 delivers, the output voltage increases above the nominal setting output voltage. The HM5167 extends its off time of the switching period to deliver less energy to the output and regulate the output voltage to 0.7% higher than the nominal setting voltage. With the PFM operation mode, the HM5167 keeps the efficiency above 80% even when the load current decreases to 1 mA. In addition, the output voltage ripple is much smaller at light load due to low peak current.

2.2. Enable and Startup (EN and SS pin)

The HM5167 has an adjustable soft start function to prevent high inrush current during start-up. To minimize the inrush current during start-up, an external capacitor, connected to the SS pin and charged with a constant current, is used to slowly ramp up the internal positive input of the error amplifier. The larger the capacitance at the SS pin, the slower the ramp of the output voltage and the longer the soft-start time. A 47-nF capacitor is usually sufficient for most applications.

When the EN pin is pulled into logic low (below 0.4V), the HM5167 goes into the shutdown mode and stops switching. Only when EN pin is pulled into logic high (above 1.5V), the HM5167 works.

2.3. Adjustable Switching Frequency (FSW pin)

This device features a wide adjustable switching frequency ranging from 200 kHz to 1.4MHz. The switching frequency is set by a resistor (R_{FREQ}) connected between the FSW pin and the SW pin of the HM5167. R_{FREQ} must always be connected from the FSW pin to SW pin for proper operation. R_{FREQ} can be calculated by:

$$R_{FREQ} = \frac{4 \times \left(\frac{1}{f_{SW}} - t_{DELAY} \times \frac{V_{OUT}}{V_{IN}} \right)}{C_{FREQ}}$$

where

- R_{FREQ} is the resistance connected between the FSW pin and the SW pin.
- $C_{FREQ} = 23\text{pF}$.
- f_{SW} is the desired switching frequency.
- $t_{DELAY} = 89 \text{ ns}$.
- V_{IN} is the input voltage.
- V_{OUT} is the output voltage.

NOTE: A resistor value of 180-300k is recommended for R_{FREQ} to get a f_{SW} of around 450-700kHz.

2.4. Load Disconnect Gate Driver (DIS pin)

The HM5167 provides a DIS pin to drive the external FET at the output side, which completely disconnects the output from the input end during shutdown or output short happens. During the device's start-up phase, the disconnect FET is controlled by the gate driver voltage of the external disconnect FET, there is an internal 60μA (typical) sink current. The load disconnect FET connection is shown as Figure 1. **Do make sure that C_{OUT2} should be no larger than $10 \times C_{OUT1}$ to avoid the inrush current when turning on the disconnect FET.**

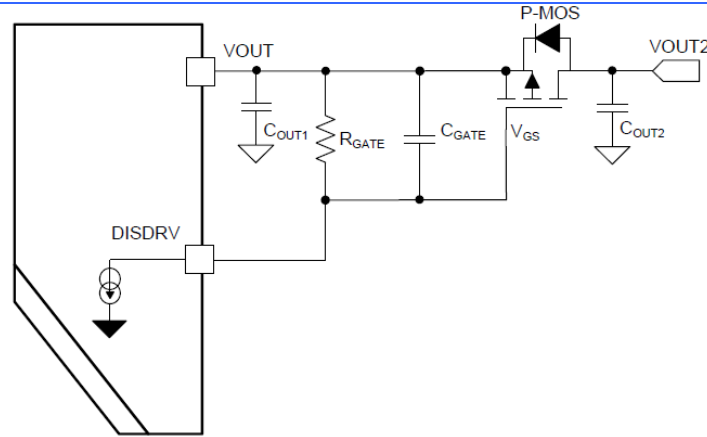


Figure 1 Load Disconnect FET Connection

The FET parameter should be considered as follows:

- The drain-to-source voltage rating V_{DS} should be higher than the output max. voltage V_{OUT} .
- The drain-to-source RMS current rating $I_{DS}(RMS)$ should be higher than the maximum output current.

The driver voltage and turn on / off timing can be set via the resistor R_{GATE} and capacitor C_{GATE} connecting between with the DIS pin and the source of the external FET. 150K and 22nF can be used in most cases.

To set the C_{GATE} , the following equation can be used:

$$C_{GATE} \approx C_{GS_PFET} = \frac{T_{ON_PFET} \times I_{DIS_PFET}}{V_{TH_PFET}}$$

where

- C_{GS_PFET} is the total gate capacitance of connected between gate and source external FET. (including the self-gate-source capacitance of the FET). The maximum capacitance C_{GS_PFET} should be < 100nF.
- T_{ON_PFET} is the turn on time of external FET. The max T_{ON_PFET} should not exceed 3ms
- I_{DIS_PFET} is the discharge current inside of HM5167, it is 60μA typically.
- V_{TH_PFET} is the gate threshold of external FET.

To set the R_{GATE} , the following equation can be used:

$$R_{GATE} = \frac{V_{GATE}}{I_{DIS_PFET}}$$

While DIS is not used, it can be connected to GND so that a more integral GND plane can be achieved to decrease the loop of output peak current.

2.5. Adjustable Peak Current Limit (ILIM pin)

To avoid an accidental large peak current, an internal cycle-by-cycle current limit is adopted. The low-side switch is turned off immediately as soon as the switch current touches the limit. The peak switch current limit can be set by a resistor (R_{ILIM}) at the ILIM pin to ground. The relationship between the current limit and the resistance is as follows:

$$I_{LIM} = \frac{1070000}{R_{ILIM}}$$

2.6. Output Voltage Setting (FB pin)

The output voltage is set by an external resistor divider (R_{UP} , R_{DN} in the Typical Application Circuit). To get the output voltage V_{OUT} , the Value of R_{UP} and R_{DN} can be calculated as:

$$V_{OUT} = V_{REF} \times \left(1 + \frac{R_{UP}}{R_{DN}}\right)$$

Where $V_{REF} = 1.204V$.

Some typical output voltages can be set as the following parameters.

$V_{OUT}(V)$	$R_{UP}(\Omega)$	$R_{DN}(\Omega)$
5.3	510k	150k
7.4	510k	100k
9.4	510k	75k
12.2	510k	56k

2.7. Inductor Selection (SW pin)

Because the selection of the inductor affects the power supply's steady state operation, transient behavior, loop stability, and boost converter efficiency, the inductor is the most important component in switching power regulator design. Three most important specifications to the performance of the inductor are the inductor value, DC resistance, and saturation current.

To be simplified, the inductor value can be set as 2.2uH which can be used in most cases.

The rated current, especially the saturation current should be larger than the peak current during the whole operation. The peak current can be calculated as follows.

$$I_{Lpeak} = I_{DC} + \frac{I_{PP}}{2}$$

$$I_{DC} = \frac{V_{OUT} \times I_{OUT}}{V_{IN} \times \eta}$$

$$I_{PP} = \frac{1}{L \times \left(\frac{1}{V_{OUT} - V_{IN}} + \frac{1}{V_{IN}}\right) \times f_{SW}}$$

Boost converter efficiency is affected significantly by the inductor's DC resistance (DCR), equivalent series resistance (ESR) at the switching frequency, and the core loss. An inductor with lower DCR and ESR would increase the efficiency significantly.

The inductor should be placed as close as possible to the SW pin. **For a lower EMI radiation, connecting a resistor and a capacitor in series to the ground would be helpful.** 1ohm resistor and 10nF capacitor would be recommended in most cases.

2.8. Input Capacitor Selection (V_{IN} , VCC pin)

For good input voltage filtering and small voltage ripple (less than 100mV is required), we recommend low-ESR capacitors of 1uF//10uF//10uF//470uF ("//" represents paralleled) be placed as close as possible to the inductor.

The V_{IN} pin is the power supply for the HM5167, a 1uF paralleled with 10uF ceramic capacitor should be placed as close as possible to the V_{IN} pin. Notice that the maximum voltage of V_{IN} should be lower than 13V. A resistor of 100R is recommended between input power supply and V_{IN} pin so that the power supply of HM5167 would be more stable. An extensive power supply such as the logic power supply connecting to V_{IN} would be another choice.

The VCC pin is the output of internal LDO. A ceramic capacitor of 2.2uF is required at the VCC pin to get a stable operation of LDO.

2.9. Output Capacitor Selection (V_{OUT} pin)

To be simplified, we recommend low-ESR capacitors of 1uF//10uF//10uF//470uF ("/" represents paralleled) be placed as close as possible to V_{OUT} pin for small output voltage ripple.

Capacitors can lose most of their capacitance at rated voltage. Therefore, leave margin on the voltage rating to ensure adequate effective capacitance.

In detail, for the require output voltage ripple, use the following equations to calculate the minimum required effective capacitance C_{OUT}

$$V_{ripple_dis} = \frac{(V_{OUT} - V_{IN_MIN}) \times I_{OUT}}{V_{OUT} \times f_{SW} \times C_{OUT}}$$

$$V_{ripple_ESR} = I_{Lpeak} \times R_{C_ESR}$$

Where

- V_{ripple_dis} is output voltage ripple caused by charging and discharging of the output capacitor.
- V_{ripple_ESR} is output voltage ripple caused by ESR of the output capacitor.
- V_{IN_MIN} is the minimum input voltage of boost converter..
- V_{OUT} is the output voltage..
- I_{OUT} is the output current.
- I_{Lpeak} is the peak current of the inductor.
- f_{SW} is the converter switching frequency.
- R_{C_ESR} is the ESR of the output capacitors.

2.10. Loop Stability (COMP pin)

The HM5167 requires external compensation, which allows the loop response to be optimized for each application. The COMP pin is the output of the internal error amplifier. An external compensation network comprised of resistor R_C, ceramic capacitors C_C and C_P is connected to the COMP pin.

To be simplified, R_C is 56kΩ, C_C is 3.3nF, and C_P can be floating. **But notice that this setting can only be adopted in most cases.** In detail, the compensation network parameters can be calculated as follows.

(1) Set the cross over frequency, f_c

The first step is to set the loop crossover frequency, f_c. The higher crossover frequency, the faster the loop response is. It is generally accepted that the loop gain cross over no higher than the lower of either 1/10 of the switching frequency, f_{SW}, or 1/5 of the RHPZ frequency, f_{RHPZ}. It's proper to use a fixed parameter of 10kHz for f_c.

$$f_{RHPZ} = \frac{R_O \times (1 - D)^2}{2\pi \times L}$$

(2) Set the compensation resistor, R_C.

$$R_C = \frac{2\pi \times V_{OUT} \times R_{sense} \times f_c \times C_O}{(1 - D) \times V_{REF} \times G_{EA}}$$

(3) Set the compensation zero capacitor, C_C

$$C_C = \frac{R_O \times C_O}{2 \times R_C}$$

(4) Set the compensation pole capacitor, C_P

$$C_P = \frac{R_{ESR} \times C_O}{R_C}$$

If the C_P is less than 10pF, it can be left open.

- R_O is the output load resistance.
- D is the switching duty cycle. $1 - D = V_{IN} / V_{OUT}$
- R_{sense} is the equivalent internal current sense resistor, which is 0.084 Ω .
- C_O is output capacitor.
- V_{REF} is the reference voltage at the FB pin, which is 1.204V.
- G_{EA} is the amplifier's transconductance, which is 190uA/V.
- R_{ESR} is the equivalent series resistance of the output capacitor.

2.11. Selecting the Bootstrap Capacitor (BOOT pin)

The bootstrap capacitor (C_{BST}) between the BOOT and SW pin supplies the gate current to charge the high-side FET device gate during each cycle's turn-on and supplies charge for the bootstrap capacitor. The recommended value of the bootstrap capacitor is 0.1 μ F to 1 μ F. C_{BST} should be a good quality, low ESR, ceramic capacitor located at the pins of the device to minimize potentially damaging voltage transients caused by trace inductance. A value of 0.1 μ F can be used in most cases.

2.12. Protection Function

Under-voltage Lockout (UVLO)

The UVLO circuit prevents the device from malfunctioning at low input voltage and the battery from excessive discharge. The HM5167 has both V_{IN} UVLO function and VCC UVLO function. It disables the device from switching when the falling voltage at the V_{IN} pin trips the UVLO threshold V_{IN_UVLO} , which is typically 2.4V. The device starts operating when the rising voltage at the V_{IN} pin is 200mV above the V_{IN_UVLO} . It also disables the device when the falling voltage at the VCC pin trips the UVLO threshold V_{CC_UVLO} , which is typically 2.1V.

Over-voltage Protection

If the output voltage at the VOUT pin is detected above 14.2 V (typical value), the HM5167 stops switching immediately until the voltage at the VOUT pin drops the hysteresis value lower than the output overvoltage protection threshold. This function prevents overvoltage on the output and secures the circuits connected to the output from excessive overvoltage.

Thermal Shutdown

A thermal shutdown is implemented to prevent damages due to excessive heat and power dissipation. Typically, the thermal shutdown happens at a junction temperature of 150°C. When the thermal shutdown is triggered, the device stops switching until the junction temperature falls below typically 130°C, then the device starts switching again.

3. Application Notes

3.1. Radiated EMI Reduction

(1) Minimize High di/dt Path Loop Area

EMI Starts off from high di/dt loops. The high di/dt critical path locates as the red circle showed in the following figure. The output capacitor should be placed as close to the VOUT pin as possible resulting in minimum area of the high di/dt loop.

The DIS pin (when not used) and NC pin can be connected to PGND ground plane which is good for thermal dissipation, can reduce the impedance of the return path and make the placement of the output capacitors easier.

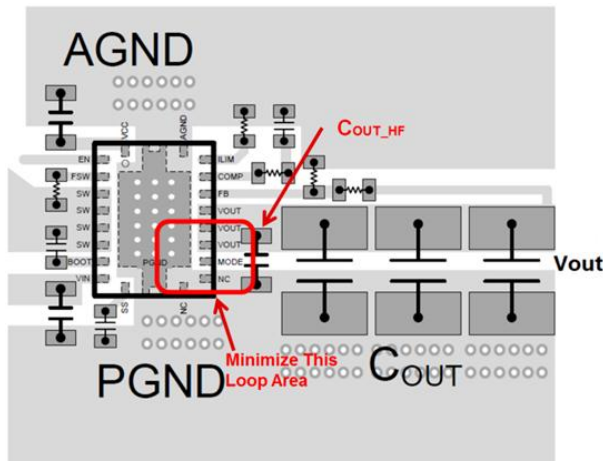


Figure 2 Critical Path Layout

(2) PCB Trace and Ground Plane

High trace inductance leads to poor radiation EMI. The inductance of a PCB trace is a function of its length and width. So, increase the trace width and decrease the trace length will significantly decrease the radiation EMI.

Meanwhile, good designed ground planes will help decrease the radiation EMI too:

- Placing a solid ground plane with minimum distance to the critical trace;
- Wider and bigger ground plane result in smaller signal trace inductance;
- Thinner insulation thickness between the ground plane and the signal traces also results in smaller inductance;

(3) RC Snubber

Adding an RC snubber across the SW pin and the power ground can help reduce the radiation EMI levels. The RC snubber should be placed as close as possible to the switching node and the power ground.

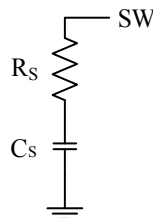


Figure 3 Placement of RC Snubber

The aim of the snubber resistor RS is to add sufficient damping to the parasitic resonant circuit. The value of RS depends on the desired damping factor and the parasitic inductor LP and parasitic capacitor CP of the circuit:

$$R_S = \frac{1}{\xi} \times \sqrt{\frac{L_P}{C_P}}$$

Where ξ is the damping factor, normally can range from 0.5 to 1.

The value of L_P and C_P can be measured by:

- Measure the original ringing frequency f_{RING} ;
- Add some small capacitance from switch node to ground. Keep increasing capacitance until the ringing frequency is 50% of the original ringing frequency f_{RING} , and the capacitance is C_S , $C_P = 1/(3C_S)$;
- $$L_P = \frac{1}{C_P \times (2\pi \times f_{RING})^2}$$

To be simplified, a resistor of 1ohm (R_S) and a capacitor of 2.2nF (C_S) can be used. However, notice that larger C_S results in higher power loss.

(4) Radiation from Cables

A longer input or output cables result in poor radiation EMI. So, make the length of input cable and output cable very close to the real application.

(5) Ferrite Bead

Ferrite Bead is used in series with the power line. Before using a ferrite bead, you need to consider about the specifications of the bead as follows:

- The frequency characteristics

Make sure that the resistive impedance of the bead is much higher than the reactive impedance in the noise frequency range.

- The rated current

Make sure that the rated current of the bead should be at least 30% higher than the expected maximum current.

- The DC resistance

The DC resistance of the ferrite bead should be as low as possible.

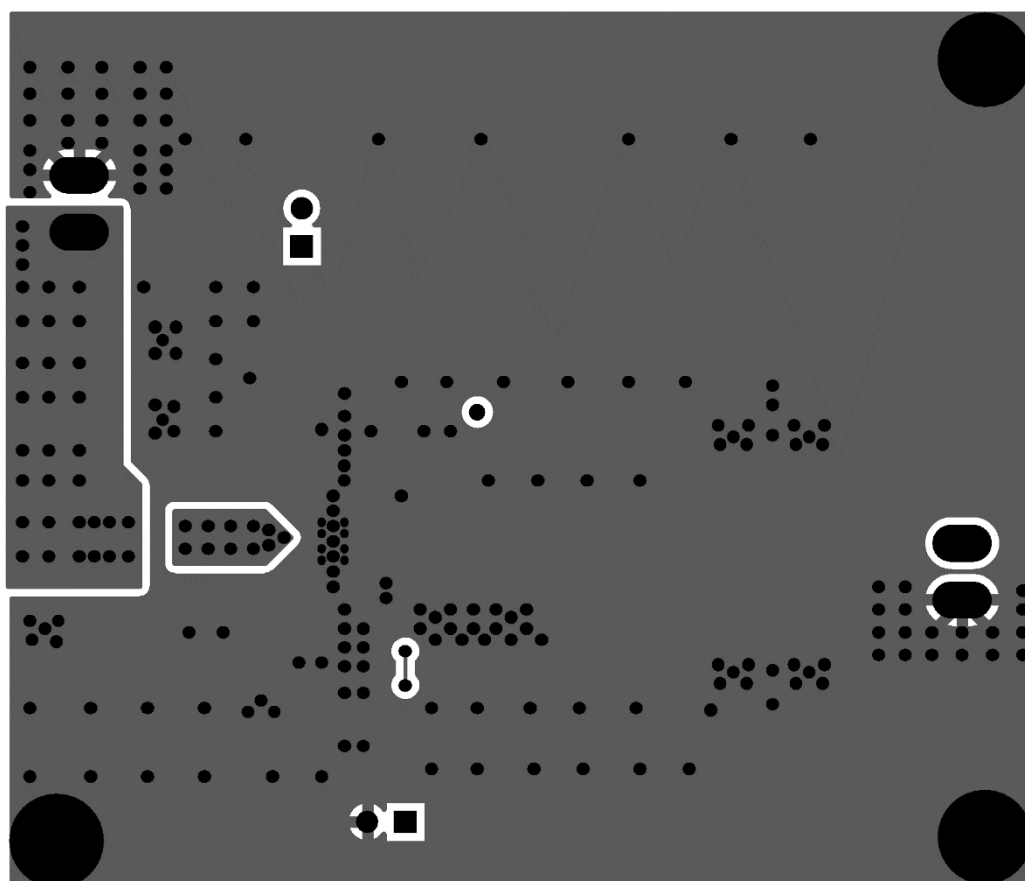
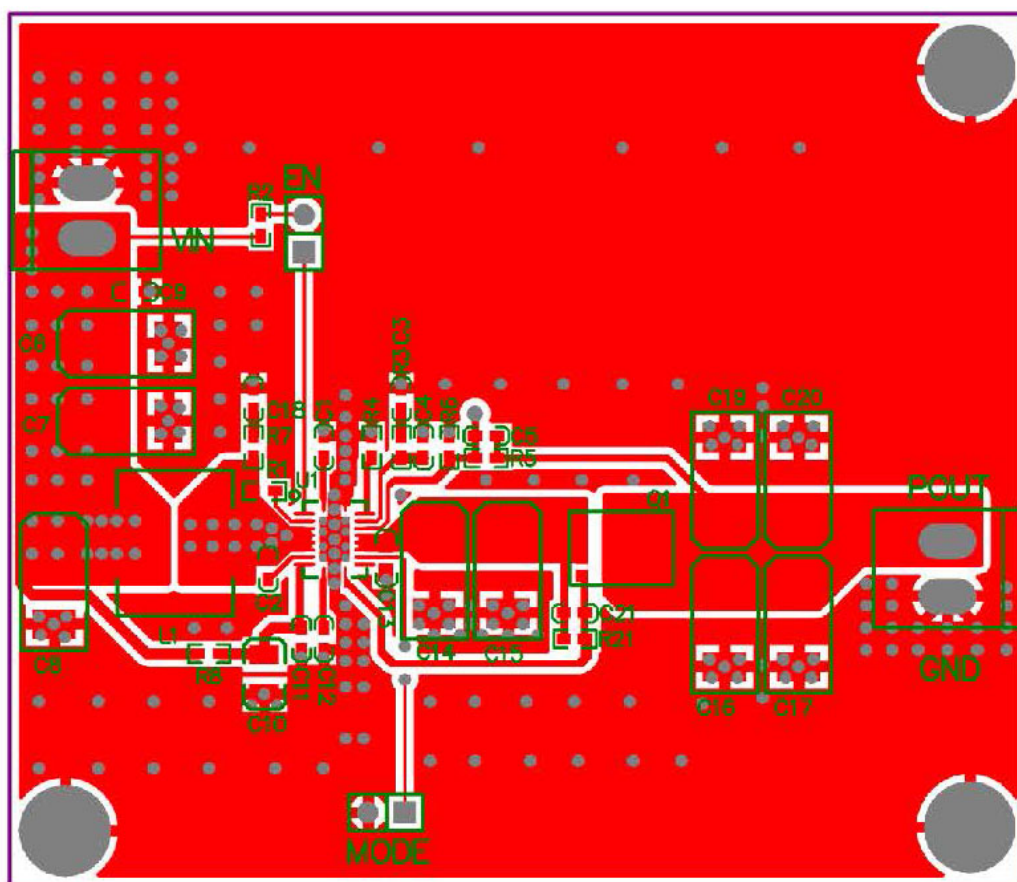
3.2. Layout Guidelines

As for all switching power supplies, especially those running at high switching frequency and high currents, layout is an important design step. If layout is not carefully done, the regulator could suffer from instability and noise problems. To maximize efficiency, switch rise and fall times are very fast. To prevent radiation of high frequency noise (for example, EMI), proper layout of the high-frequency switching path is essential. Minimize the length and area of all traces connected to the SW pin, and always use a ground plane under the switching regulator to minimize interplane coupling.

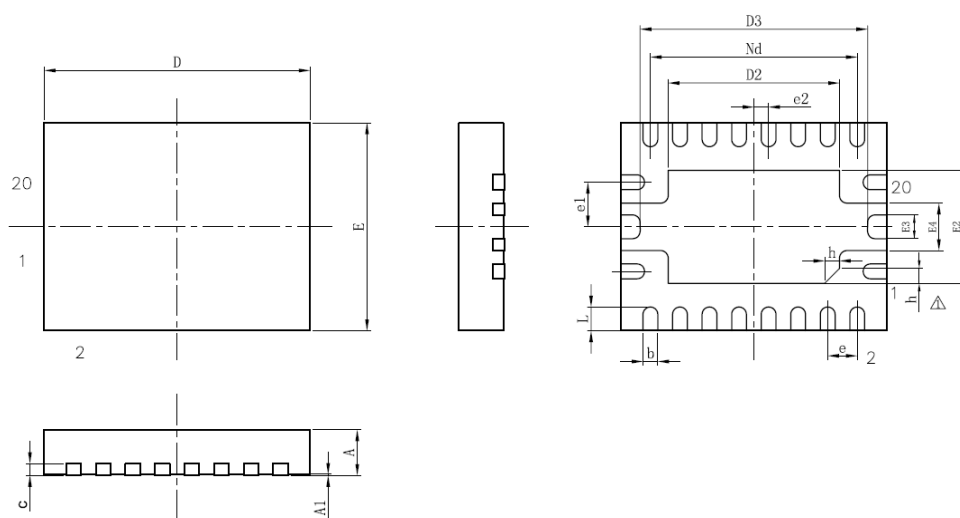
The input capacitor needs to be close to inductor L, the V_{IN} pin and GND pin in order to reduce the input supply ripple. The output capacitor needs to be close to V_{OUT} pin and GND pin in order to reduce the output supply ripple.

The layout should also be done with well consideration of the thermal as this is a high-power density device. A thermal pad that improves the thermal capabilities of the package should be soldered to the large ground plate, using thermal vias underneath the thermal pad.

3.3. Layout Examples



■ PACKAGE OUTLINE



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	—	0.01	0.05
b	0.18	0.25	0.30
c	0.18	0.20	0.25
D	4.40	4.50	4.60
D2	3.10	3.20	3.30
D3	3.85REF		
e	0.50BSC		
e1	0.75BSC		
e2	0.25BSC		
Nd	3.50BSC		
E	3.40	3.50	3.60
E2	2.10	2.20	2.30
E3	0.35REF		
E4	0.75REF		
L	0.35	0.40	0.45
h	0.20	0.25	0.30
载体尺寸 (mil)	134*94		